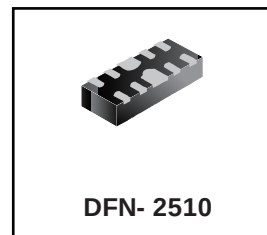




4-CHANNEL LOW CAPACITANCE ESD PROTECTION DIODES ARRAY

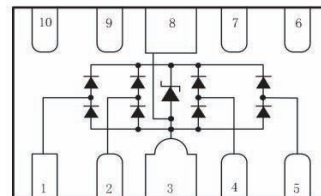
The FTV8804DFN2510 is a 4- channel ultra low capacitance rail clam ESD protection diodes array. Each channel consists of a pair of diodes that steer positive or negative ESD current to either the positive or negative rail . A zener diode is integrated in to the array between the positive and negative supply rails. In the typical applications, the negative rail pin (assigned as GND) is connected with system ground . The Positive ESD current is steered to the ground through an ESD diode and Zener diode and the positive ESD voltage is clamped to the zener voltage. The FTV8804DFN2510 is idea to protect high speed data lines.



● APPLICATIONS

- 1) HDMI / DVI ports
- 2) Display Port interface
- 3) 10M / 100M / 1G Ethernet
- 4) USB 2.0 interface
- 5) VGA interface
- 6) Set- top box
- 7) Flat panel Monitors / TVs
- 8) PC / Note book

PIN CONFIGURATION



● FEATURES

- 1) 4 channels of ESD protection;
- 2) Provides ESD protection to IEC61000- 4- 2 level 4
 - $\pm 15\text{kV}$ air discharge
 - $\pm 15\text{kV}$ contact discharge;
- 3) Channel I/O to GND capacitance: 0.6pF(Max)
- 4) Channel I/O to I/O capacitance: 0.3pF(Max)
- 5) Low clamping voltage;
- 6) Low operating voltage;
- 7) Improved zener structure;
- 8) Optimized package for easy high speed data lines PCB layout;
- 9) RoHS compliant.

● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
FTV8804DFN2510	24B	3000 Tape&Reel



● ABSOLUTE MAXIMUM RATINGS

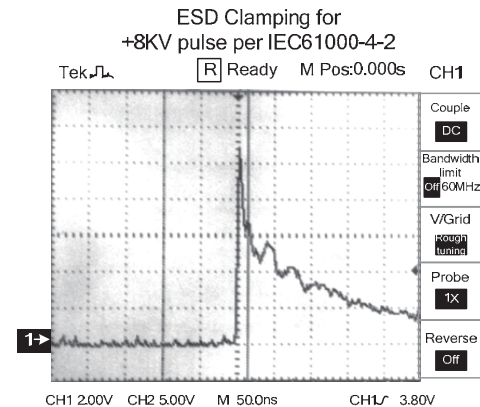
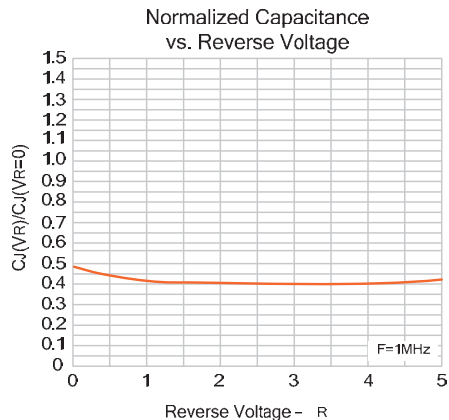
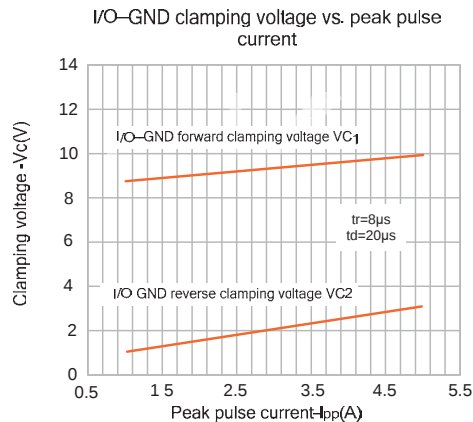
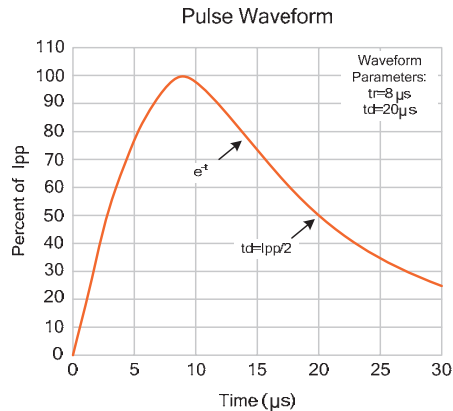
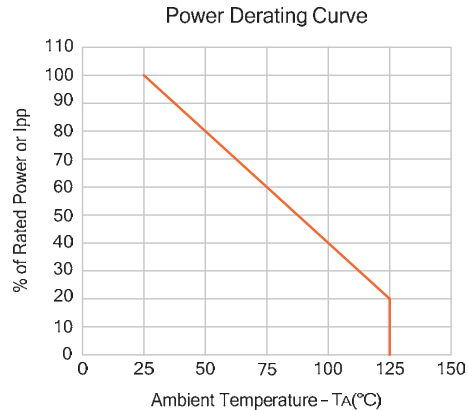
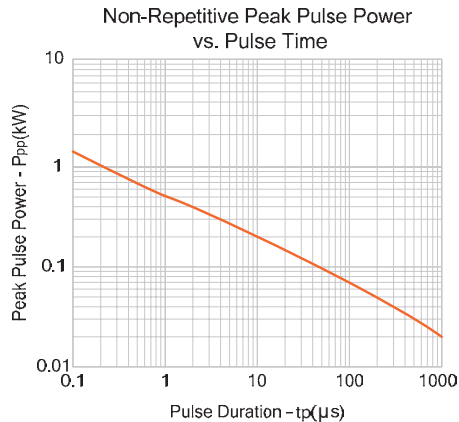
Parameter	Symbol	Limits	Unit
Peak Pulse Power(8/20us)	PPP	75	W
Peak Pulse Current(8/20us)	I _{PP}	5	A
ESD per IEC 61000-4-2(Air)	VESD1	±15kV	kV
ESD per IEC 61000-4-2(Contact)	VESD2	±15kV	kV
Operating Temperature Range	T _{opr}	-55~+125	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

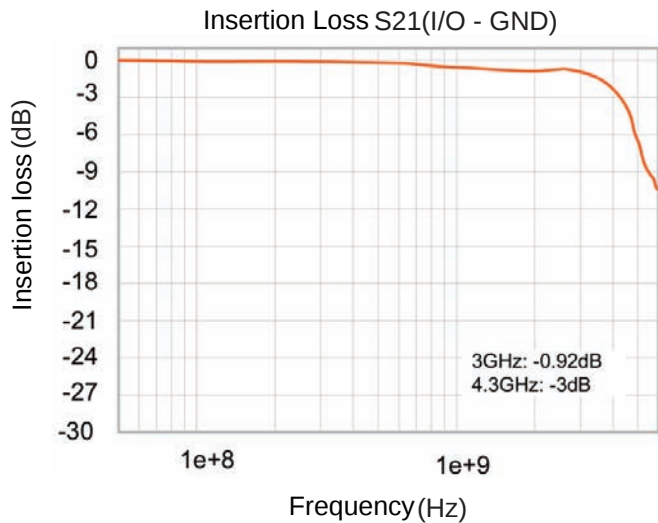
● ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Working Voltage	V _{RWM}	—	—	5.5	V	Any I/O pin to GND
Reverse Breakdown Voltage	V _{BR}	6	—	—	V	I _t =1mA; Any I/O pin to GND
Reverse Leakage Current	I _R	—	—	1	μA	V _{RWM} =5V, T=25°C; Any I/O pin to GND
Positive Clamping Voltage	V _{C1}	—	8.5	12	V	I _{PP} =1A, t _P =8/20μs; Positive pulse; Any I/O pin to GND
Negative Clamping Voltage	V _{C2}	—	1.8	—	V	I _{PP} =1A, t _P =8/20μs; Negative pulse; Any I/O pin to GND
Junction Capacitance Between Channel	C _{J1}	—	—	0.3	pF	V _R =0V, f=1MHz; Between I/O pins
Junction Capacitance Between I/O And GND	C _{J2}	—	—	0.6	pF	V _R =0V, f=1MHz; Any I/O pin to GND
Dynamic Resistance	R _{dynamic}	—	0.776	—	Ohm	Positive Transient(TLP)



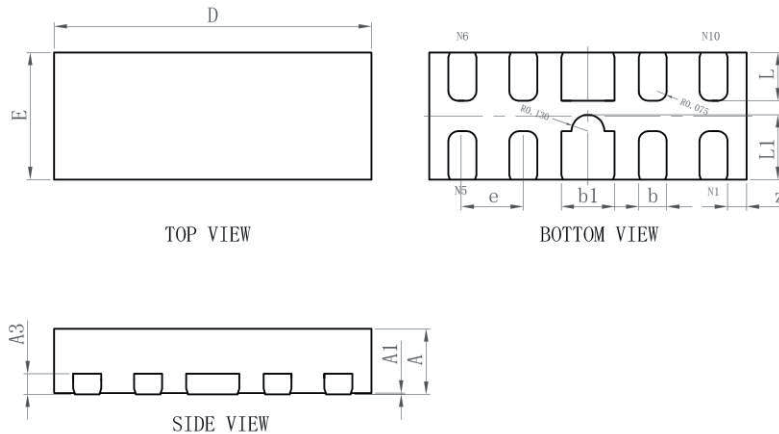
ELECTRICAL CHARACTERISTIC CURVES





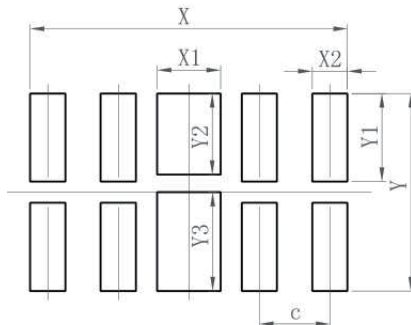
DFN-2510

Package Outline Dimension



DFN2510			
Dim	Min	Typ	Max
A	0.48	0.53	0.58
A1	0	0.02	0.05
A3	-	0.152	-
b	0.17	0.22	0.27
b1	0.37	0.42	0.47
D	2.45	2.50	2.55
e	0.45	0.50	0.55
E	0.95	1.00	1.05
L	0.33	0.38	0.43
L1	0.46	0.51	0.56
z	0.10	0.15	0.20
All Dimensions in mm			

Suggested Pad layout



DFN2510	mm
c	0.5
X	2.25
X1	0.45
X2	0.25
Y	1.4
Y1	0.625
Y2	0.575
Y3	0.7